

74HC245-Q100; 74HCT245-Q100

Octal bus transceiver; 3-state

Rev. 1 — 22 July 2013

Product data sheet

1. General description

The 74HC245-Q100; 74HCT245-Q100 is an 8-bit transceiver with 3-state outputs. The device features an output enable (\overline{OE}) and send/receive (DIR) for direction control. A HIGH on \overline{OE} causes the outputs to assume a high-impedance OFF-state. Inputs include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Octal bidirectional bus interface
- Non-inverting 3-state outputs
- Multiple package options
- Complies with JEDEC standard no. 7A
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\ \Omega$)

3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74HC245D-Q100 74HCT245D-Q100	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74HC245PW-Q100 74HCT245PW-Q100	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74HC245BQ-Q100 74HCT245BQ-Q100	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	DHVQFN20	plastic dual-in-line compatible thermal enhanced very thin quad flat package no leads; 20 terminals; body $2.5 \times 4.5 \times 0.85\text{ mm}$	SOT764-1



4. Functional diagram

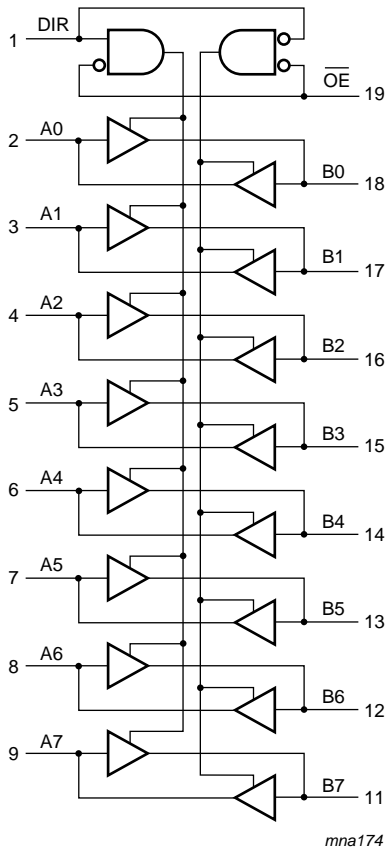


Fig 1. Logic symbol

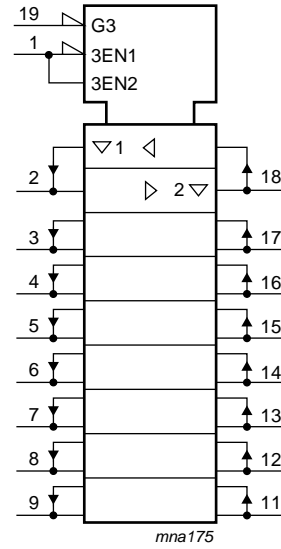


Fig 2. IEC logic symbol

5. Pinning information

5.1 Pinning

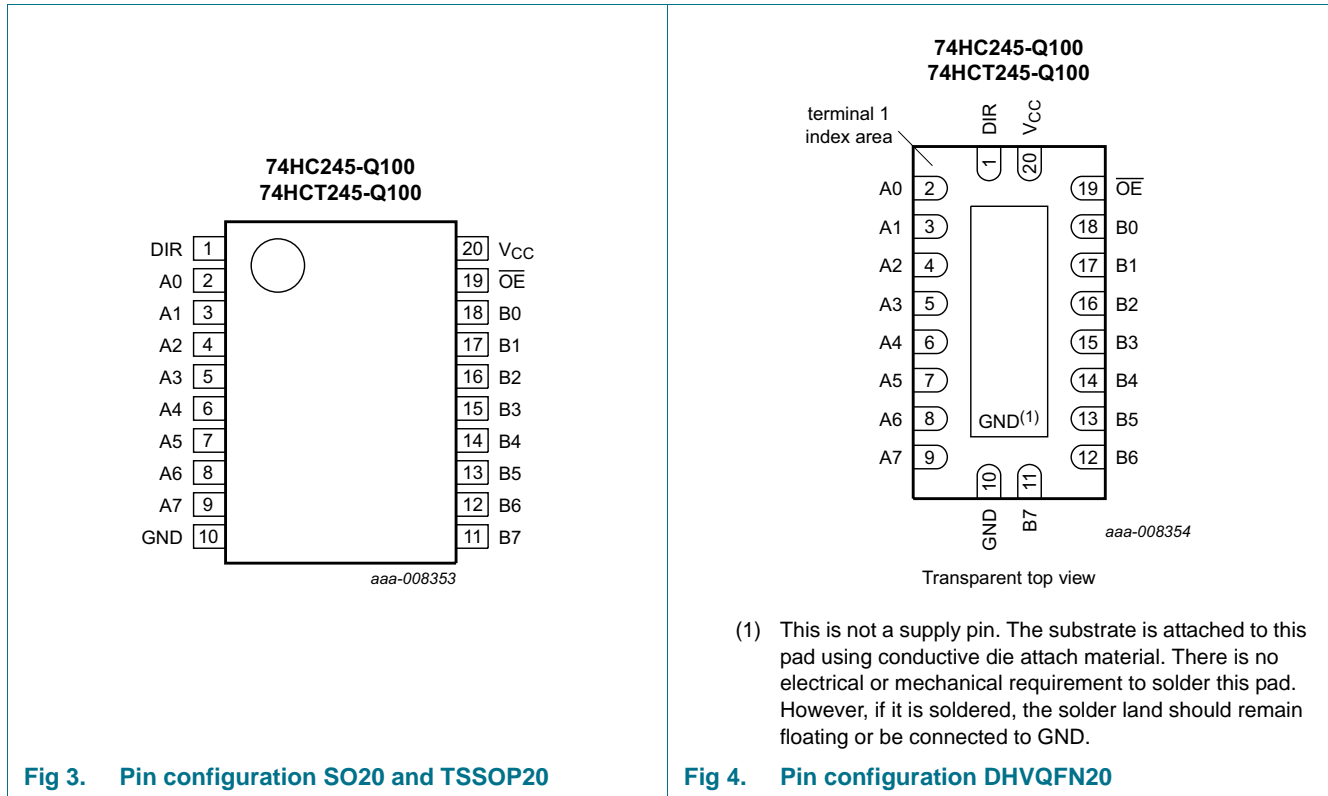


Fig 3. Pin configuration SO20 and TSSOP20

Fig 4. Pin configuration DHVQFN20

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
DIR	1	direction control
A0, A1, A2, A3, A4, A5, A6, A7	2, 3, 4, 5, 6, 7, 8, 9	data input/output
GND	10	ground (0 V)
B0, B1, B2, B3, B4, B5, B6, B7	18, 17, 16, 15, 14, 13, 12, 11	data input/output
OE	19	output enable input (active LOW)
VCC	20	supply voltage

6. Functional description

Table 3. Function table^[1]

Input		Input/output		
OE	DIR	An	Bn	
L	L	A = B	input	
L	H	input	B = A	
H	X	Z	Z	

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	-	±20	mA
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	-	±20	mA
I _O	output current	V _O = -0.5 V to V _{CC} + 0.5 V	-	±35	mA
I _{CC}	supply current		-	+70	mA
I _{GND}	ground current		-70	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	SO20, TSSOP20 and DHVQFN20 packages	[1]	-	500 mW

[1] For SO20 package: above 70 °C, P_{tot} derates linearly with 8 mW/K.
 For TSSOP20 package: above 60 °C, P_{tot} derates linearly with 5.5 mW/K.
 For DHVQFN20 package: above 60 °C, P_{tot} derates linearly with 4.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC245-Q100			74HCT245-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics type 74HC245-Q100
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 μA; V _{CC} = 2.0 V	1.9	2.0	-	V
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	4.5	-	V
		I _O = -20 μA; V _{CC} = 6.0 V	5.9	6.0	-	V
		I _O = -6.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	V
		I _O = 7.8 mA; V _{CC} = 6.0 V	-	0.16	0.26	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.5	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	μA
C _I	input capacitance		-	3.5	-	pF
C _{I/O}	input/output capacitance		-	10	-	pF
T_{amb} = -40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	V
		V _{CC} = 4.5 V	3.15	-	-	V
		V _{CC} = 6.0 V	4.2	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	V
		V _{CC} = 4.5 V	-	-	1.35	V
		V _{CC} = 6.0 V	-	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 μA; V _{CC} = 2.0 V	1.9	-	-	V
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	-	-	V
		I _O = -20 μA; V _{CC} = 6.0 V	5.9	-	-	V
		I _O = -6.0 mA; V _{CC} = 4.5 V	3.84	-	-	V
		I _O = -7.8 mA; V _{CC} = 6.0 V	5.34	-	-	V

Table 6. Static characteristics type 74HC245-Q100 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 μA; V _{CC} = 2.0 V	-	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	-	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	-	0.33	V
		I _O = 7.8 mA; V _{CC} = 6.0 V	-	-	0.33	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±1.0	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±5.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	80	μA
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	V
		V _{CC} = 4.5 V	3.15	-	-	V
		V _{CC} = 6.0 V	4.2	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	V
		V _{CC} = 4.5 V	-	-	1.35	V
		V _{CC} = 6.0 V	-	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}		-		
		I _O = -20 μA; V _{CC} = 2.0 V	1.9	-	-	V
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	-	-	V
		I _O = -20 μA; V _{CC} = 6.0 V	5.9	-	-	V
		I _O = -6.0 mA; V _{CC} = 4.5 V	3.7	-	-	V
		I _O = -7.8 mA; V _{CC} = 6.0 V	5.2	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}		-		
		I _O = 20 μA; V _{CC} = 2.0 V	-	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	-	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	-	0.4	V
		I _O = 7.8 mA; V _{CC} = 6.0 V	-	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±1.0	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±10.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	160	μA

Table 7. Static characteristics type 74HCT245-Q100

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = -20 μA	4.4	4.5	-	V
		I _O = -6 mA	3.98	4.32	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = 20 μA	-	0	0.1	V
		I _O = 6.0 mA	-	0.15	0.26	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _{CC} = 5.5 V; V _O = V _{CC} or GND per input pin; other inputs at V _{CC} or GND; I _O = 0 A	-	-	±0.5	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	8.0	μA
ΔI _{CC}	additional supply current	per input pin; V _I = V _{CC} - 2.1 V; other inputs at V _I = V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V; I _O = 0 A				
		An or Bn inputs	-	40	144	μA
		$\overline{\text{OE}}$ input	-	150	540	μA
		DIR input	-	90	324	μA
C _I	input capacitance		-	3.5	-	pF
C _{I/O}	input/output capacitance		-	10	-	pF
T_{amb} = -40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = -20 μA	4.4	-	-	V
		I _O = -6 mA	3.84	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = 20 μA	-	-	0.1	V
		I _O = 6.0 mA	-	-	0.33	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±1.0	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _{CC} = 5.5 V; V _O = V _{CC} or GND per input pin; other inputs at V _{CC} or GND; I _O = 0 A	-	-	±5.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	80	μA

Table 7. Static characteristics type 74HCT245-Q100 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1$ V; other inputs at $V_I = V_{CC}$ or GND; $V_{CC} = 4.5$ V to 5.5 V; $I_O = 0$ A				
		An or Bn inputs	-	-	180	μ A
		\overline{OE} input	-	-	675	μ A
		DIR input	-	-	405	μ A
$T_{amb} = -40$ °C to $+125$ °C						
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5$ V to 5.5 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5$ V to 5.5 V	-	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5$ V				
		$I_O = -20$ μ A	4.4	-	-	V
		$I_O = -6$ mA	3.7	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5$ V				
		$I_O = 20$ μ A	-	-	0.1	V
		$I_O = 6.0$ mA	-	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5$ V	-	-	± 1.0	μ A
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 5.5$ V; $V_O = V_{CC}$ or GND per input pin; other inputs at V_{CC} or GND; $I_O = 0$ A	-	-	± 10	μ A
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	160	μ A
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1$ V; other inputs at $V_I = V_{CC}$ or GND; $V_{CC} = 4.5$ V to 5.5 V; $I_O = 0$ A				
		An or Bn inputs	-	-	196	μ A
		\overline{OE} input	-	-	735	μ A
		DIR input	-	-	441	μ A

10. Dynamic characteristics

Table 8. Dynamic characteristics type 74HC245-Q100

$GND = 0\text{ V}$; for test circuit, see [Figure 7](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = 25\text{ °C}$						
t_{pd}	propagation delay	An to Bn or Bn to An; see Figure 5	[1]			
		$V_{CC} = 2.0\text{ V}$	-	25	90	ns
		$V_{CC} = 4.5\text{ V}$	-	9	18	ns
		$V_{CC} = 5.0\text{ V}; C_L = 15\text{ pF}$	-	7	-	ns
		$V_{CC} = 6.0\text{ V}$	-	7	15	ns
t_{en}	enable time	\overline{OE} to An or \overline{OE} to Bn; see Figure 6	[2]			
		$V_{CC} = 2.0\text{ V}$	-	30	150	ns
		$V_{CC} = 4.5\text{ V}$	-	11	30	ns
		$V_{CC} = 6.0\text{ V}$	-	9	26	ns
t_{dis}	disable time	\overline{OE} to An or \overline{OE} to Bn; see Figure 6	[3]			
		$V_{CC} = 2.0\text{ V}$	-	41	150	ns
		$V_{CC} = 4.5\text{ V}$	-	15	30	ns
		$V_{CC} = 6.0\text{ V}$	-	12	26	ns
t_t	transition time	An, Bn; see Figure 5	[4]			
		$V_{CC} = 2.0\text{ V}$	-	14	60	ns
		$V_{CC} = 4.5\text{ V}$	-	5	12	ns
		$V_{CC} = 6.0\text{ V}$	-	4	10	ns
C_{PD}	power dissipation capacitance	$V_I = GND$ to V_{CC}	[5]	-	30	pF
$T_{amb} = -40\text{ °C to }+85\text{ °C}$						
t_{pd}	propagation delay	An to Bn or Bn to An; see Figure 5	[1]			
		$V_{CC} = 2.0\text{ V}$	-	-	115	ns
		$V_{CC} = 4.5\text{ V}$	-	-	23	ns
		$V_{CC} = 6.0\text{ V}$	-	-	20	ns
t_{en}	enable time	\overline{OE} to An or \overline{OE} to Bn; see Figure 6	[2]			
		$V_{CC} = 2.0\text{ V}$	-	-	190	ns
		$V_{CC} = 4.5\text{ V}$	-	-	38	ns
		$V_{CC} = 6.0\text{ V}$	-	-	33	ns
t_{dis}	disable time	\overline{OE} to An or \overline{OE} to Bn; see Figure 6	[3]			
		$V_{CC} = 2.0\text{ V}$	-	-	190	ns
		$V_{CC} = 4.5\text{ V}$	-	-	38	ns
		$V_{CC} = 6.0\text{ V}$	-	-	33	ns

Table 8. Dynamic characteristics type 74HC245-Q100 ...continuedGND = 0 V; for test circuit, see [Figure 7](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_t	transition time	An, Bn; see Figure 5	[4]			
		$V_{CC} = 2.0\text{ V}$	-	-	75	ns
		$V_{CC} = 4.5\text{ V}$	-	-	15	ns
		$V_{CC} = 6.0\text{ V}$	-	-	13	ns
$T_{amb} = -40\text{ °C to }+125\text{ °C}$						
t_{pd}	propagation delay	An to Bn or Bn to An; see Figure 5	[1]			
		$V_{CC} = 2.0\text{ V}$	-	-	135	ns
		$V_{CC} = 4.5\text{ V}$	-	-	27	ns
		$V_{CC} = 6.0\text{ V}$	-	-	23	ns
t_{en}	enable time	\overline{OE} to An or \overline{OE} to Bn; see Figure 6	[2]			
		$V_{CC} = 2.0\text{ V}$	-	-	225	ns
		$V_{CC} = 4.5\text{ V}$	-	-	45	ns
		$V_{CC} = 6.0\text{ V}$	-	-	38	ns
t_{dis}	disable time	\overline{OE} to An or \overline{OE} to Bn; see Figure 6	[3]			
		$V_{CC} = 2.0\text{ V}$	-	-	225	ns
		$V_{CC} = 4.5\text{ V}$	-	-	45	ns
		$V_{CC} = 6.0\text{ V}$	-	-	38	ns
t_t	transition time	An, Bn; see Figure 5	[4]			
		$V_{CC} = 2.0\text{ V}$	-	-	90	ns
		$V_{CC} = 4.5\text{ V}$	-	-	18	ns
		$V_{CC} = 6.0\text{ V}$	-	-	15	ns

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .[2] t_{en} is the same as t_{PZH} and t_{PZL} .[3] t_{dis} is the same as t_{PLZ} and t_{PHZ} .[4] t_t is the same as t_{THL} and t_{TLH} .[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

 f_i = input frequency in MHz; f_o = output frequency in MHz; C_L = output load capacitance in pF; V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

Table 9. Dynamic characteristics type 74HCT245-Q100GND = 0 V; for test circuit, see [Figure 7](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
T_{amb} = 25 °C							
t _{pd}	propagation delay	An to Bn or Bn to An; see Figure 5	[1]				
		V _{CC} = 4.5 V	-	12	22	ns	
		V _{CC} = 5.0 V; C _L = 15 pF	-	10	-	ns	
t _{en}	enable time	\overline{OE} to An or \overline{OE} to Bn; V _{CC} = 4.5 V; see Figure 6	[2]	-	16	30	ns
t _{dis}	disable time	\overline{OE} to An or \overline{OE} to Bn; V _{CC} = 4.5 V; see Figure 6	[3]	-	16	30	ns
t _t	transition time	An, Bn; V _{CC} = 4.5 V; see Figure 5	[4]	-	5	12	ns
C _{PD}	power dissipation capacitance	V _I = GND to V _{CC} - 1.5 V	[5]	-	30	-	pF
T_{amb} = -40 °C to +85 °C							
t _{pd}	propagation delay	V _{CC} = 4.5 V; see Figure 5	[1]	-	-	28	ns
t _{en}	enable time	\overline{OE} to An or \overline{OE} to Bn; V _{CC} = 4.5 V; see Figure 6	[2]	-	-	38	ns
t _{dis}	disable time	\overline{OE} to An or \overline{OE} to Bn; V _{CC} = 4.5 V; see Figure 6	[3]	-	-	38	ns
t _t	transition time	An, Bn; V _{CC} = 4.5 V; see Figure 5	[4]	-	-	15	ns
T_{amb} = -40 °C to +125 °C							
t _{pd}	propagation delay	V _{CC} = 4.5 V; see Figure 5	[1]	-	-	33	ns
t _{en}	enable time	\overline{OE} to An or \overline{OE} to Bn; V _{CC} = 4.5 V; see Figure 6	[2]	-	-	45	ns
t _{dis}	disable time	\overline{OE} to An or \overline{OE} to Bn; V _{CC} = 4.5 V; see Figure 6	[3]	-	-	45	ns
t _t	transition time	An, Bn; V _{CC} = 4.5 V; see Figure 5	[4]	-	-	18	ns

[1] t_{pd} is the same as t_{PLH} and t_{PHL}.[2] t_{en} is the same as t_{PZH} and t_{PZL}.[3] t_{dis} is the same as t_{PLZ} and t_{PHZ}.[4] t_t is the same as t_{THL} and t_{TLH}.[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

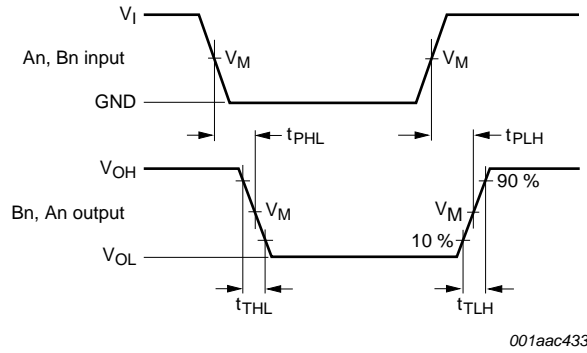
$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;f_o = output frequency in MHz;C_L = output load capacitance in pF;V_{CC} = supply voltage in V;

N = number of inputs switching;

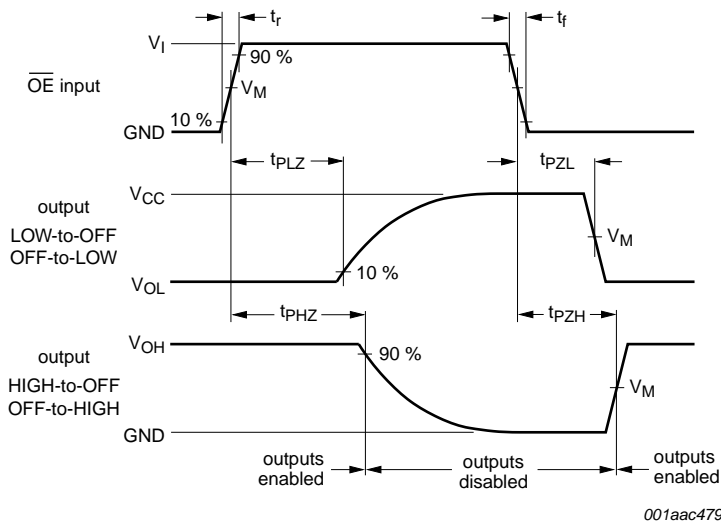
 $\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms



Measurement points are given in [Table 10](#).
 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 5. Input (An, Bn) to output (Bn, An) propagation delays and output transition times

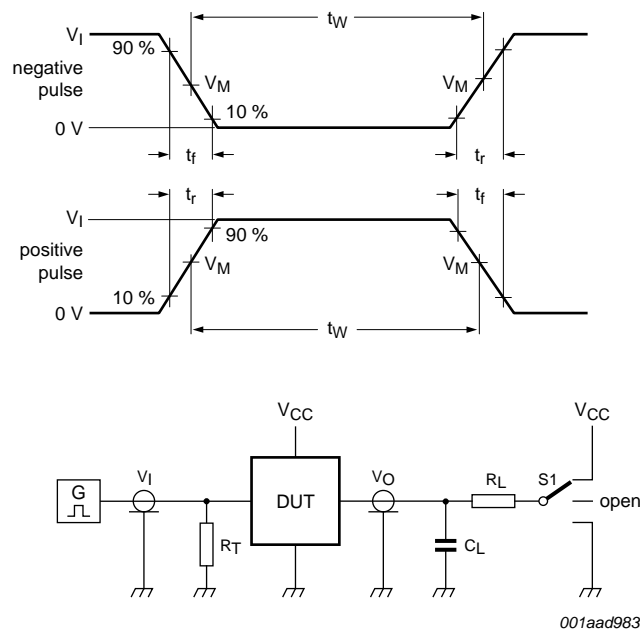


Measurement points are given in [Table 10](#).
 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. 3-state output enable and disable times

Table 10. Measurement points

Type	Input	Output
	V_M	V_M
74HC245-Q100	$0.5V_{CC}$	$0.5V_{CC}$
74HCT245-Q100	1.3 V	1.3 V



Test data is given in [Table 11](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 7. Test circuit for measuring switching times

Table 11. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC245-Q100	V_{CC}	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}
74HCT245-Q100	3 V	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}

12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1

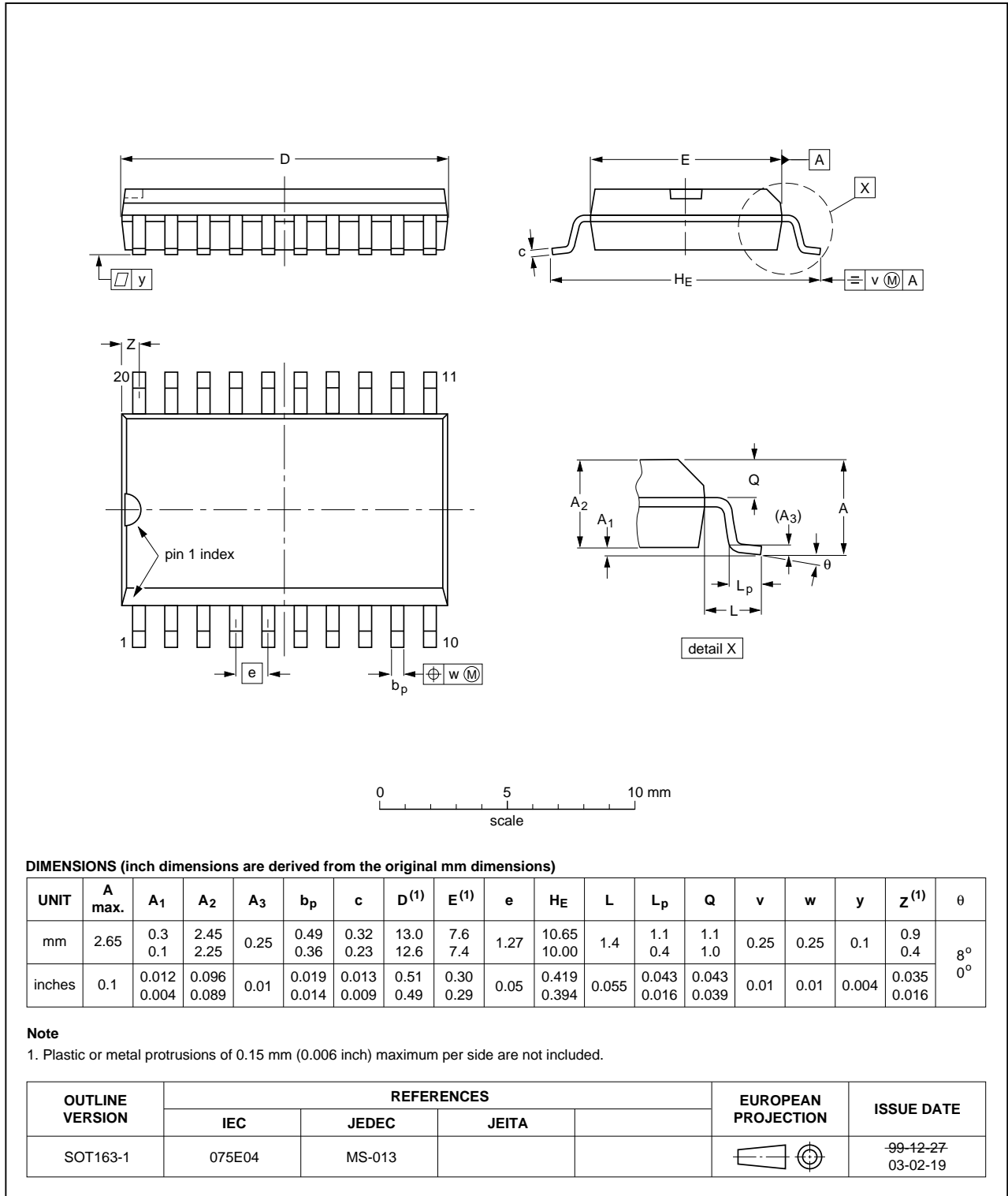


Fig 8. Package outline SOT163-1 (SO20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1

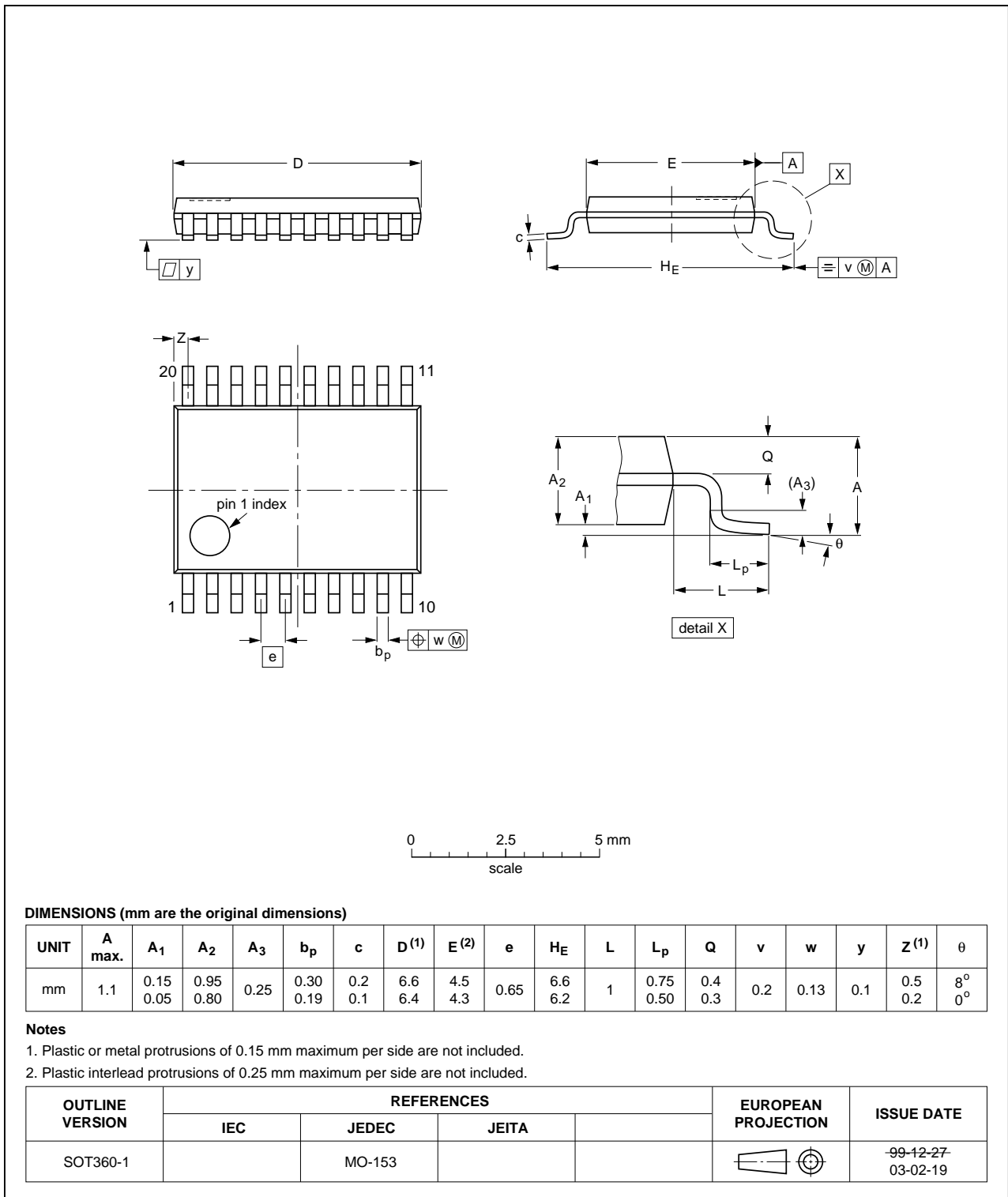


Fig 9. Package outline SOT360-1 (TSSOP20)

DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm

SOT764-1

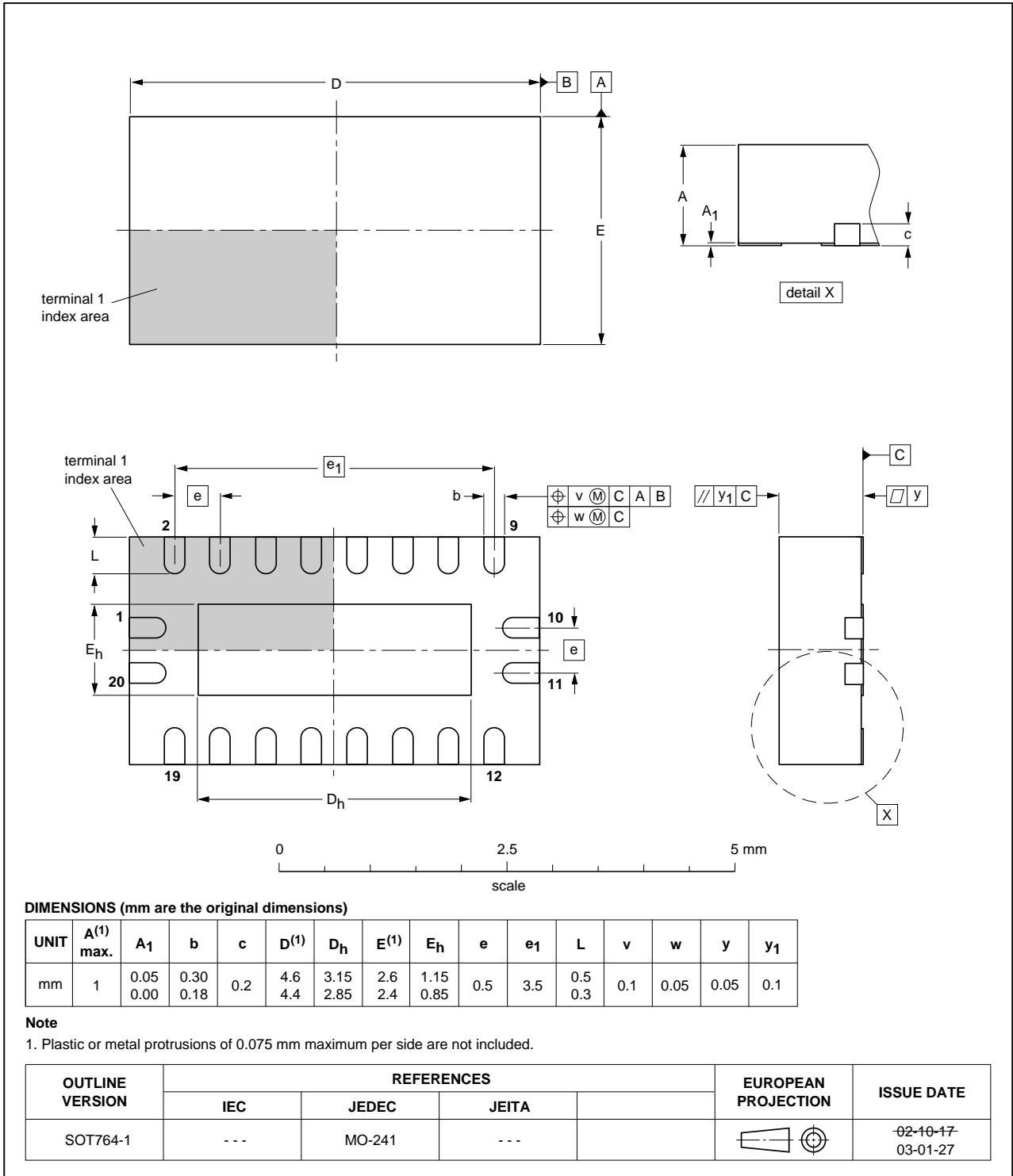


Fig 10. Package outline SOT764-1 (DHVQFN20)

13. Abbreviations

Table 12. Abbreviations

Acronym	Description
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
MIL	Military

14. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT245_Q100 v.1	20130722	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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